

L Number	Hits	Search Text	JB	Time stamp
1	114	(156/345.12,156/345.31, 156/345.32).ccls.	USPAT	2002/10/22 12:27
2	1667	438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88	USPAT	2002/10/22 12:28
3	1708	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)	USPAT	2002/10/22 12:28
4	194	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and ((thickness depth metrology) same (clean\$3 buff\$3 wash\$3 rins\$3))	USPAT	2002/10/22 12:30
5	408	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 clean\$3)	USPAT	2002/10/22 12:34
6	59	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and ((thickness depth metrology) same (clean\$3 buff\$3 wash\$3 rins\$3))) and (((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 clean\$3))	USPAT	2002/10/22 12:31
7	211	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and ((thickness depth metrology) same (clean\$3 buff\$3 wash\$3 rins\$3))) and (((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 clean\$3))) and (elevator cassette vertical\$2)	USPAT	2002/10/22 12:32
8	31	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and ((thickness depth metrology) same (clean\$3 buff\$3 wash\$3 rins\$3))) and (((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 clean\$3))) and (elevator cassette vertical\$2)	USPAT	2002/10/22 12:33
9	38	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 and clean\$3)	USPAT	2002/10/22 12:44
10	9770	(planariz\$5 polish\$3) same (clean\$3 rins\$3 wash\$3)	EPO; JPO; DERWENT	2002/10/22 12:53
11	1815	((planariz\$5 polish\$3) same (clean\$3 rins\$3 wash\$3)) and (semiconductor wafer)	EPO; JPO; DERWENT	2002/10/22 12:55
12	73	((planariz\$5 polish\$3) same (clean\$3 rins\$3 wash\$3)) and (semiconductor wafer)) and (thickness metrology depth width) with (clean\$3 rins\$3 wash\$3)	EPO; JPO; DERWENT	2002/10/22 12:55